LISTING OF CLAIMS

1. (Canceled)

2. (Currently amended) A transistor ~~microdevice~~ for forming a part of an integrated circuit, comprising:

a first conductive region forming a source and a second conductive region forming a drain having a channel region interposed therebetween; and

a channel region controlling component forming a gate electrode disposed over the channel region and separated therefrom by at least one dielectric layer, wherein the channel region controlling component has a non-linear structural characteristic derived from a non-linear structural characteristic of a photo resist feature used as an etch mask for the channel region controlling component,

wherein the non-linear characteristic of the photo resist feature is selected to provide ~~provides~~ mechanical stability to the photo resist feature; and

wherein at any point measured from the source to the drain in a perpendicular direction to a widthwise bisector of the gate electrode, the gate electrode defines a channel length having a substantially constant dimension.

3. (Original) The microdevice according to claim 2, wherein the non-linear characteristic of the photo resist feature includes an arc.

4. (Original) The microdevice according to claim 2, wherein the non-linear characteristic of the photo resist feature includes a vertex.

5. (Currently amended) The microdevice according to claim 2, wherein the non-linear characteristic of the photo resist feature includes a tab extending laterally beyond a width of the photo resist feature and located with respect to the channel region controlling component outside a gate electrode portion thereof.

6. (Original) The microdevice according to claim 2, wherein the channel region controlling component is made by deconstructive patterning of one of the photo resist feature or a structure patterned using the photo resist feature.

7-9. (Canceled)

10. (Currently amended) The microdevice according to claim 2 [[8]], wherein the generally constant dimension is one of a physical dimension or an electrical dimension.

11. (Canceled)

12. (Currently amended) The microdevice according to claim 22 [[11]], wherein the flash memory device is a dielectric charge trapping flash memory device.

13-21. (Canceled)

22. (New) A flash memory device for forming a part of an integrated circuit, comprising:

a plurality of conductive regions forming bit lines with a channel region interposed between adjacent pairs of bit lines; and

a word line arranged transverse to each bit line and disposed over each channel region to form a control gate therefor, the word line separated from each channel region by at least one dielectric layer and a charge storing layer, wherein the word line has a non-linear structural characteristic derived from a non-linear structural characteristic of a photo resist feature used as an etch mask for the channel region controlling component,

wherein the non-linear characteristic of the photo resist feature is selected to provide mechanical stability to the photo resist feature; and

wherein the non-linear structural characteristic displaces the word line along a longitudinal axis thereof and each channel has substantially the same channel length as defined by the word line.

23. (New) The flash memory device according to claim 22, wherein each channel is defined by a local portion of the word line that has electrical linearity.

24. (New) The flash memory device according to claim 22, wherein the non-linear structural characteristic of the word line forms a repeating pattern along the longitudinal axis of the of the word line.

25. (New) The flash memory device according to claim 22, wherein the non-linear characteristic of the photo resist feature includes an arc.

26. (New) The flash memory device according to claim 22, wherein the non-linear characteristic of the photo resist feature includes a vertex.

27. (New) The flash memory device according to claim 22, wherein the non-linear characteristic of the photo resist feature includes a tab extending laterally beyond a width of the photo resist feature and located with respect to the word line outside the control gate portions thereof.